



Description

Designed for use as output devices in complementary general purpose amplifier applications.

Features:

- · High gain darlington performance
- High DC current gain hFE = 1,000 (Minimum) at Ic = 20A
- · Monolithic construction with built-in base-emitter shunt resistor

Maximum Ratings

Characteristic	Symbol	MJ11016	Unit
Collector-Emitter Voltage	V _{CEO}	120	
Collector-Base Voltage	V _{CBO}	120	V
Emitter-Base Voltage	V_{EBO}	5	
Collector Current -Continuous -Peak	I _C I _{CM}	30 50	А
Base Current	I _B	1	
Total Power Dissipation @T _c = 25°C Derate above 25°C	P_D	200 1.15	W W/°C
Operating and Storage Junction Temperature Range	T_J,T_STG	-65 to +200	°C

Thermal Characteristics

Characteristic	Symbol	Maximum	Unit
Thermal Resistance Junction to Case	Rθjc	0.87	°C/W







Electrical Characteristics (TC = 25°C unless otherwise noted)

Characteristic	Symbol	Minimum	Maximum	Unit
Off Characteristics				
Collector-Emitter Sustaining Voltage (1) $(I_C=100\text{mA}, I_B=0)$ MJ11016	V _{EO (sus)}	120	-	V
Collector Cutoff Current (V _{CE} = 50 V, I _B = 0)	I _{CEO}	-	1	
	I _{CER}	-	1 5	mA
Emitter Cutoff Current ($V_{EB} = 5V$, $I_C = 0$)	I _{EBO}	-	5]

On Characteristrics (1)

DC Current Gain (I _C = 20A,V _{CE} = 5V) (I _C = 30A,V _{CE} = 5V)	h _{FE}	1,000 200	-	-
Collector-Emitter Saturation Voltage ($I_C = 20A$, $I_B = 200mA$) ($I_C = 30A$, $I_B = 300mA$)	V _{CE (sat)}	-	3 4	V
Base-Emitter Saturation Voltage ($I_C = 20A$, $I_B = 200mA$) ($I_C = 30A$, $I_B = 300mA$)	V _{BE (sat)}	-	3.5 5	

Dynamic Characteristics

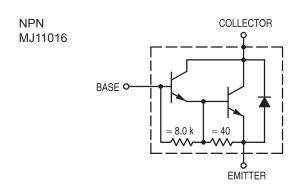
Small-Signal Current Gain	lb l	4		
$(I_C = 10A, V_{CE} = 3V, f = 1MHz)$	h _{fe}	4	-	-

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(1) Pulse Test: Pulse Width = 300µs, Duty Cycle 2%.

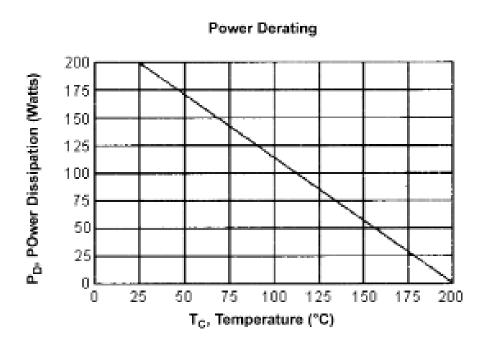
(2) $f_T = |h_{fe}| \cdot ftest$.

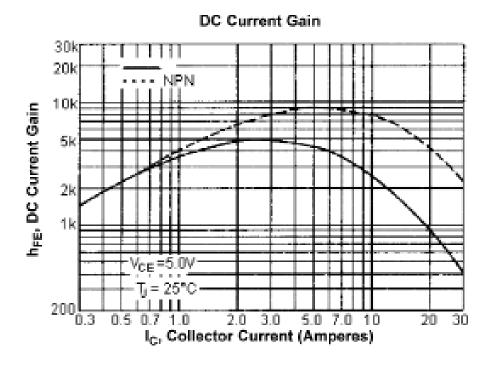
Internal Schematic Diagram







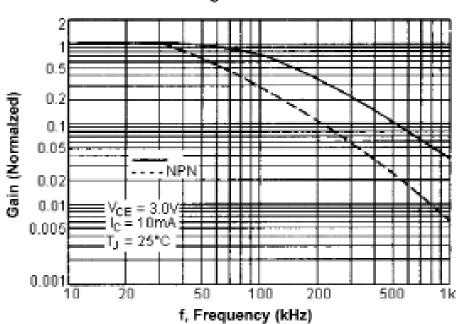




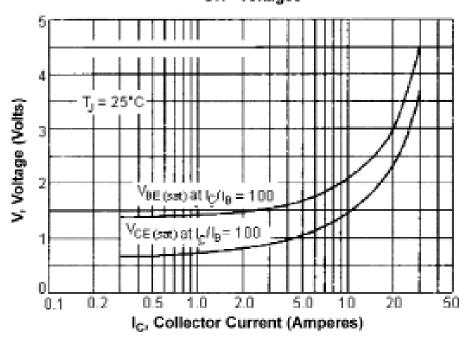




Small-Signal Current Gain

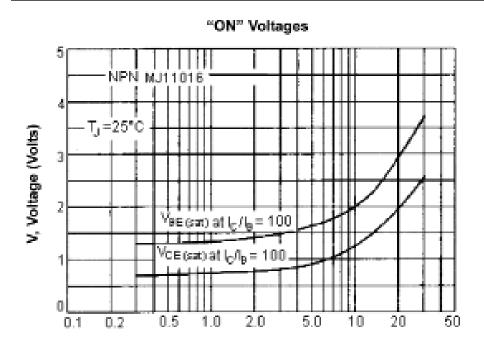


"ON" Voltages

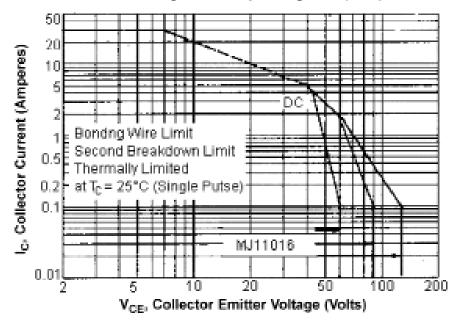


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Active-Region Safe Operating Area (SOA)

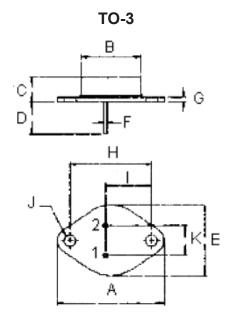


There are two limitation on the power handling ability of a transistor: average junction temperature and second breakdown safe operating area curves indicate Ic-VcE limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than curves indicate.

The data of SOA curve is base on $T_{J(PK)} = 200^{\circ}C$; TC is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(PK)} \le 200^{\circ}C$. At high case temperatures, thermal limitation will reduce the power that can be handled to values less than the limitations imposed by second breakdown.







Dimensions	Minimum	Maximum
Α	38.75	39.96
В	19.28	22.23
С	7.96	9.28
D	11.18	12.19
E	25.2	26.67
F	0.92	1.09
G	1.38	1.62
Н	29.9	30.4
I	16.64	17.3
J	3.88	4.36
K	10.67	11.18

Pin 1. Base

- 2. Emitter
- 3. Collector (Case)

Part Number Table

Description	Part Number
Darlington Transistor, TO-3	MJ11016

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